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PATENT

Customer ID: 25094

2815

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

O I P E JCB7
APR 18 2002
PATENTS & TRADEMARKS

In re Application of:

Martin E. Kordesch et al.

Application No.

09/682,151

Filing Date:

July 27, 2001

Group Art Unit:

2815

Examiner:

Chu, Chris C.

Title:

**CONTACT METHOD FOR THIN SILICON
CARBIDE EPITAXIAL LAYER AND
SEMICONDUCTOR DEVICES FORMED BY
THOSE METHODS**

Certification Under 37 C.F.R. § 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner for Patents, Washington, D.C. 20231, on Apr. 10, 2002.

Carolyn J. Williams
Carolyn J. Williams

Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

AMENDMENT

This Amendment is filed in regard to United States Patent Application No. 09/682,151 entitled "Contact Method for Thin Silicon Carbide Epitaxial Layer and Semiconductor Devices Formed by Those Methods" filed July 27, 2001. Please enter this Amendment into the current Application.

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IN THE SPECIFICATION:

Please insert the following paragraph on page 1 before "BACKGROUND OF INVENTION":

GOVERNMENTAL RIGHTS

a1
The U.S. Government has a paid-up license in this invention and the right in limited circumstances to require the patent owner to license others on reasonable terms as provided by the terms of F33615-01-C-1602 awarded by the Air Force Research Laboratory.